TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSⅢ)

# **TPCA8102**

Lithium Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- · Small footprint due to small and thin package
- Low drain-source ON resistance: RDS (ON) =  $4.5 \text{m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 60S$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \mu A (max) (V_{DS} = -30 V)$
- Enhancement mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V (V}_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA})$

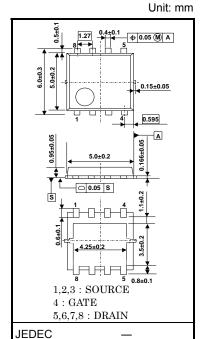
#### Maximum Ratings (Ta = 25°C)

Characte	ristics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	-30	V	
Drain-gate voltage (R	$k_{GS} = 20 \text{ k}\Omega$	$V_{DGR}$	-30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	I <sub>D</sub>	<b>- 40</b>	Α	
Diam current	Pulsed (Note 1)	$I_{DP}$	-120	A .	
Drain power dissipati	on (Tc=25°C)	$P_{D}$	45	W	
Drain power dissipation	on (t = 10 s) (Note 2a)	$P_{D}$	2.8	W	
Drain power dissipation	on (t = 10 s) (Note 2b)	$P_{D}$	1.6	W	
Single pulse avalanch	ne energy (Note 3)	EAS	208	mJ	
Avalanche current		I <sub>AR</sub>	<b>- 40</b>	Α	
Repetitive avalanche	energy c=25°C) (Note 4)	E <sub>AR</sub>	4.5	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

Note: For (Note 1), (Note 2), (Note 3), (Note 4), please refer to the next page.

This transistor is an electrostatic sensitive device. Please handle with caution.

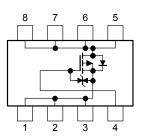
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Weight: 0.076 g (typ.)

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#### **Circuit Configuration**

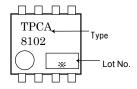


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#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

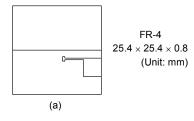
### Marking (Note 5)

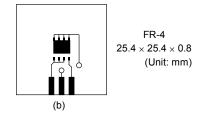


Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)



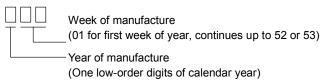


Note 3:  $V_{DD}=24~V,~T_{ch}=25^{\circ}C$  (initial),  $L=100\,\mu$  H,  $R_{G}=25~\Omega,~I_{AR}=-40~A$ 

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: O on lower left of the marking indicates Pin 1.

Weekly code: (Three digits)



## **Electrical Characteristics (Ta = 25°C)**

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-OFF cu	rrent	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	— — –10		μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$ -30	_	_	V	
Diam-30dice bice	akdown voltage	V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-15	_	_	V
Gate threshold vo	oltage	$V_{th}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8 — -2.0		V	
Drain-source ON	rosistanos	Pro (OLI)	$V_{GS} = -4 \text{ V}, I_D = -20 \text{ A}$		9.0	14	mΩ
Diain-source ON	resistance	NDS (ON)	$V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	_	4.5	6.0	11122
Forward transfer	Forward transfer admittance		$V_{DS} = -10 \text{ V}, I_D = -20 \text{ A}$	30	60	_	S
Input capacitance	•	C <sub>iss</sub>		_	4600	_	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	850	_	pF
Output capacitance		C <sub>oss</sub>		_	980	_	
	Rise time	t <sub>r</sub>	$V_{GS}$ $0 \text{ V}$ $\Gamma$ $I_D = -20 \text{A}$	_	10	_	
	Turn-ON time	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	_				
Switching time	Fall time	t <sub>f</sub>	#4.7 S	-10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	ns	
	Turn-OFF time	t <sub>off</sub>		_	220	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	109		nC
Gate-source charge 1		Q <sub>gs1</sub>		_	24	_	
Gate-drain ("miller") charge		Q <sub>gd</sub>			25	_	

### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	-120	Α
Forward voltage (diode)			V <sub>DSF</sub>	$I_{DR} = -40 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V

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4